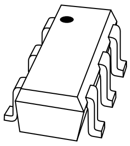


PMGD780SN

Dual N-channel µTrenchMOS standard level FET

Rev. 02 — 19 April 2010 **Product data sheet**

1. Product profile

1.1 General description

Dual N-channel enhancement mode field-effect transistor in a small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using TrenchMOS technology.

1.2 Features and benefits

- Surface-mounted package
- Standard level threshold voltage
- Low on-state resistance
- Footprint 40 % smaller than SOT23
- Fast switching
- Dual device

1.3 Applications

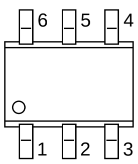
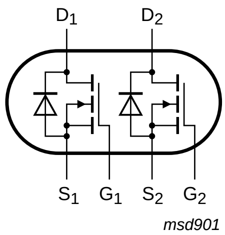
- Driver circuits
- Switching in portable appliances

1.4 Quick reference data

- $V_{DS} \leq 60$ V
- $P_{tot} \leq 0.41$ W
- $I_D \leq 0.49$ A
- $R_{DSon} \leq 920$ mΩ

2. Pinning information

Table 1. Pinning - SOT363 (SC-88), simplified outline and symbol

Pin	Description	Simplified outline	Graphic symbol
1	source1 (S1)		
2	gate1 (G1)		
3	drain2 (D2)		
4	source2 (S2)		
5	gate2 (G2)		
6	drain1 (D1)	**SOT363 (SC-88)**	

3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
PMGD780SN	SC-88	plastic surface-mounted package; 6 leads	SOT363

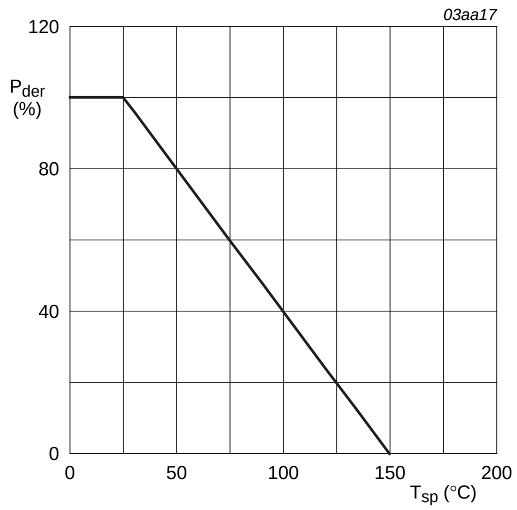
4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

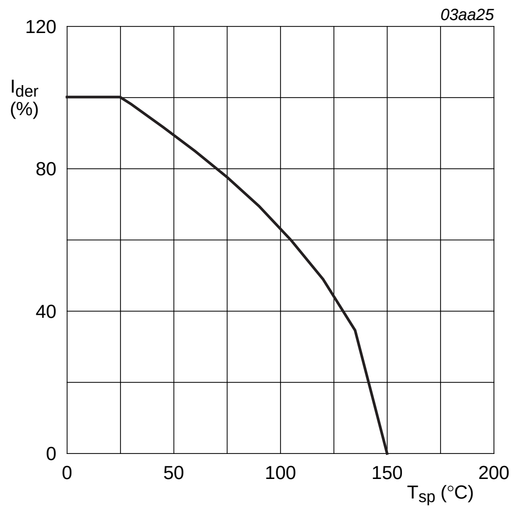
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 150 °C		-	60	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 150 °C; R_{GS} = 20 kΩ		-	60	V
V_{GS}	gate-source voltage			-	±20	V
I_D	drain current	T_{sp} = 25 °C; V_{GS} = 10 V; Figure 2 and 3	[1]	-	0.49	A
		T_{sp} = 100 °C; V_{GS} = 10 V; Figure 2	[1]	-	0.31	A
I_{DM}	peak drain current	T_{sp} = 25 °C; pulsed; t_p ≤ 10 μs; Figure 3	[1]	-	0.99	A
P_{tot}	total power dissipation	T_{sp} = 25 °C; Figure 1		-	0.41	W
T_{stg}	storage temperature			–55	+150	°C
T_j	junction temperature			–55	+150	°C
Source-drain diode						
I_S	source current	T_{sp} = 25 °C	[1]	-	0.34	A
I_{SM}	peak source current	T_{sp} = 25 °C; pulsed; t_p ≤ 10 μs	[1]	-	0.69	A

[1] Single device conducting.



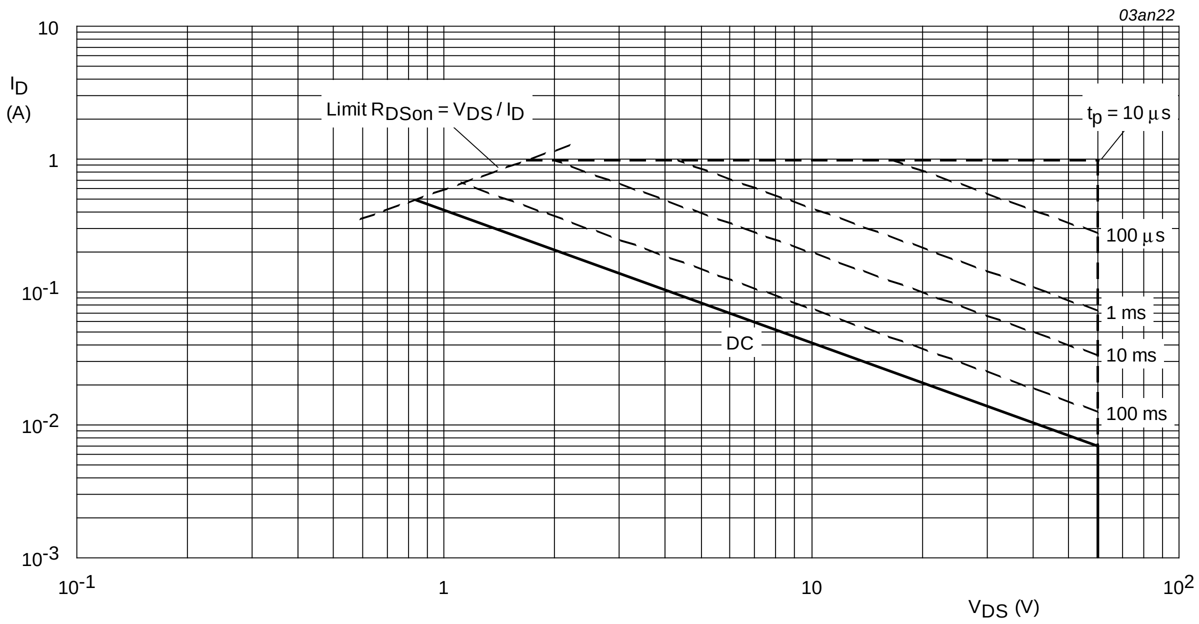
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of solder point temperature



$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of solder point temperature



T_{sp} = 25 °C; I_{DM} is single pulse; V_{GS} = 10 V

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	Figure 4	-	-	300	K/W

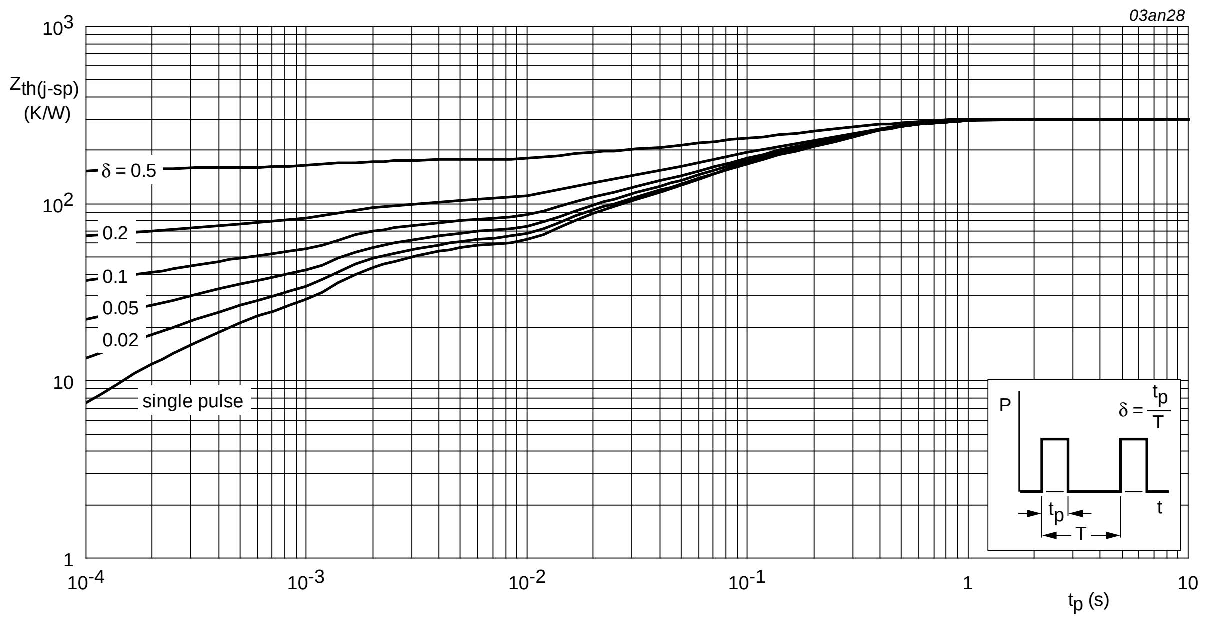


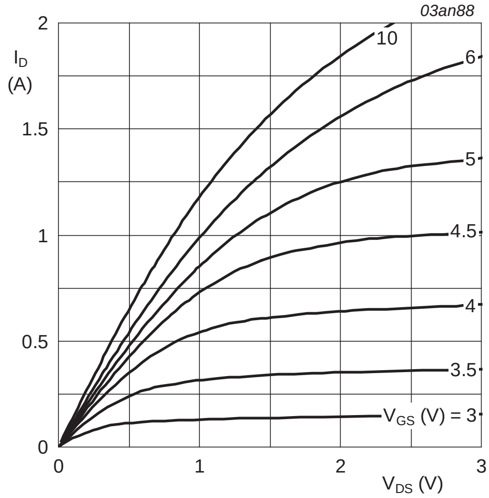
Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration

6. Characteristics

Table 5. Characteristics

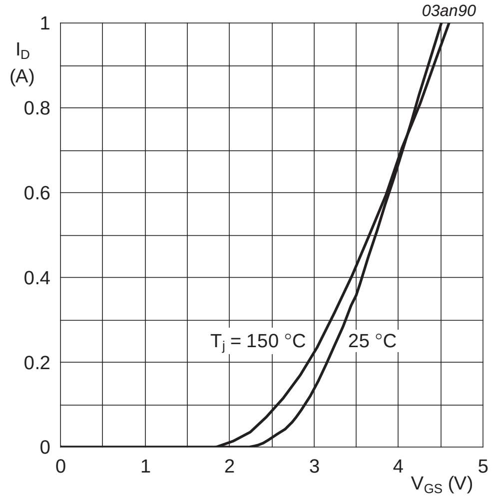
T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 μA; V_{GS} = 0 V				
		T_j = 25 °C	60	-	-	V
		T_j = –55 °C	55	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 0.25 mA; V_{DS} = V_{GS}; Figure 9				
		T_j = 25 °C	1	2	2.5	V
		T_j = 150 °C	0.6	–	–	V
		T_j = –55 °C	–	–	3.5	V
I_{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V				
		T_j = 25 °C	-	0.05	1	μA
		T_j = 150 °C	-	-	100	μA
I_{GSS}	gate leakage current	V_{GS} = ±20 V; V_{DS} = 0 V	-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 0.3 A; Figure 7 and 8				
		T_j = 25 °C	-	780	920	mΩ
		T_j = 150 °C	-	1445	1700	mΩ
		V_{GS} = 4.5 V; I_D = 0.075 A; Figure 7 and 8	-	1100	1400	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 1 A; V_{DD} = 30 V; V_{GS} = 10 V; Figure 13	-	1.05	-	nC
Q_{GS}	gate-source charge		-	0.2	-	nC
Q_{GD}	gate-drain charge		-	0.22	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 30 V; f = 1 MHz; Figure 11	-	23	-	pF
C_{oss}	output capacitance		-	5	-	pF
C_{rss}	reverse transfer capacitance		-	3.5	-	pF
$t_{d(on)}$	turn-on delay time	V_{DD} = 30 V; R_L = 30 Ω; V_{GS} = 10 V; R_G = 6 Ω	-	2	-	ns
t_r	rise time		-	4	-	ns
$t_{d(off)}$	turn-off delay time		-	5	-	ns
t_f	fall time		-	2.2	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 0.3 A; V_{GS} = 0 V; Figure 12	-	0.83	1.2	V



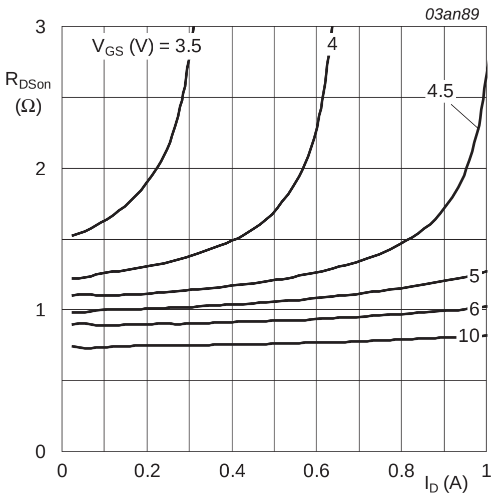
T_j = 25 °C

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



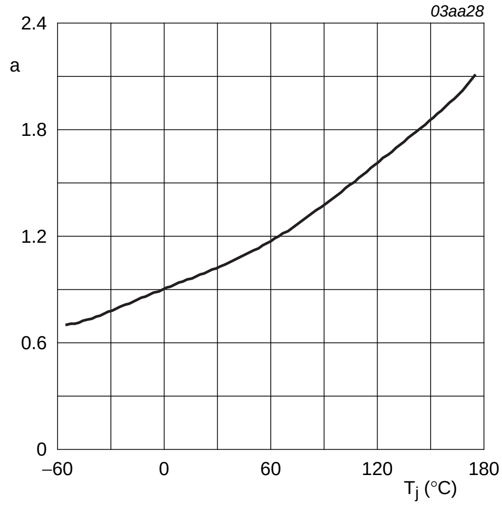
T_j = 25 °C and 150 °C; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



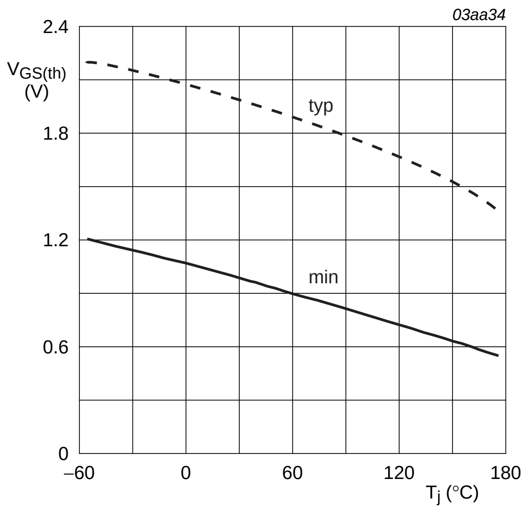
T_j = 25 °C

Fig 7. Drain-source on-state resistance as a function of drain current; typical values



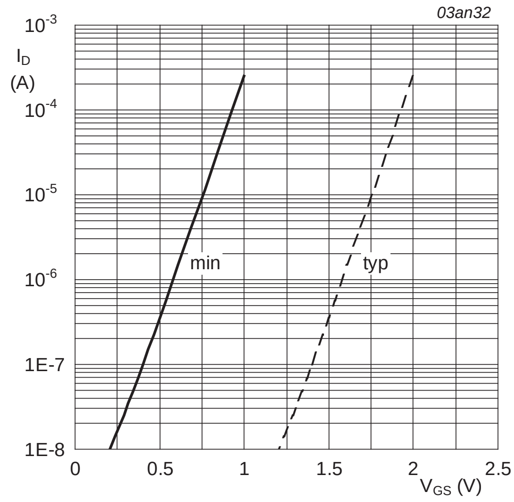
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

Fig 8. Normalized drain-source on-state resistance as a function of junction temperature



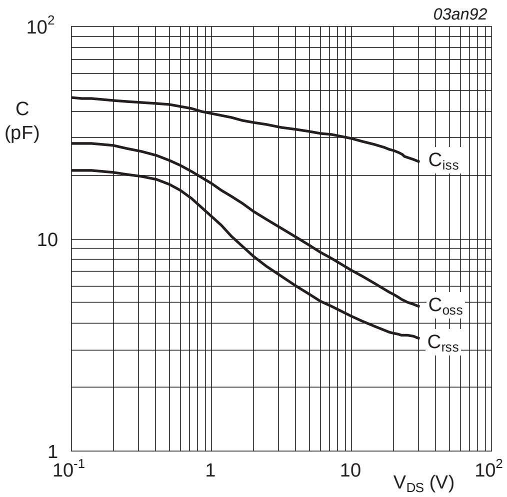
I_D = 0.25 mA; V_{DS} = V_{GS}

Fig 9. Gate-source threshold voltage as a function of junction temperature



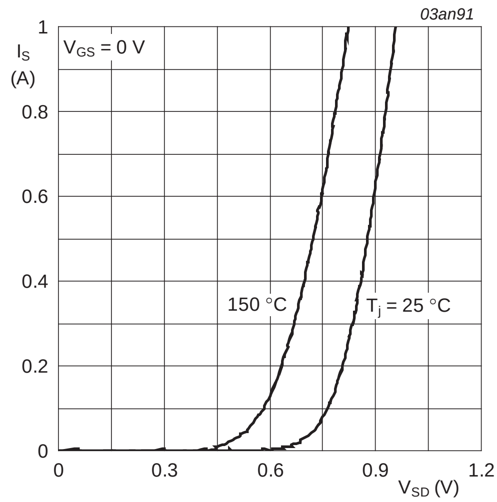
T_j = 25 °C; V_{DS} = 5 V

Fig 10. Sub-threshold drain current as a function of gate-source voltage



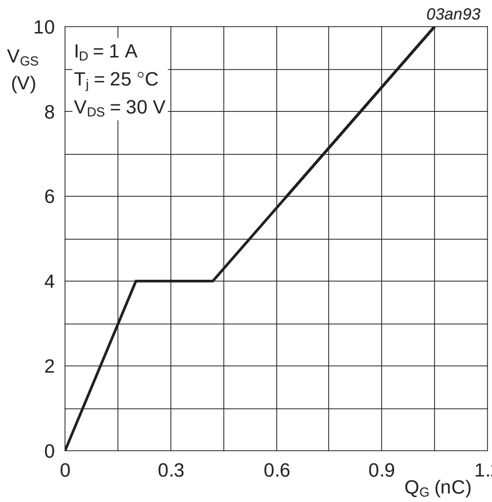
V_{GS} = 0 V; f = 1 MHz

Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



T_j = 25 °C and 150 °C; V_{GS} = 0 V

Fig 12. Source current as a function of source-drain voltage; typical values

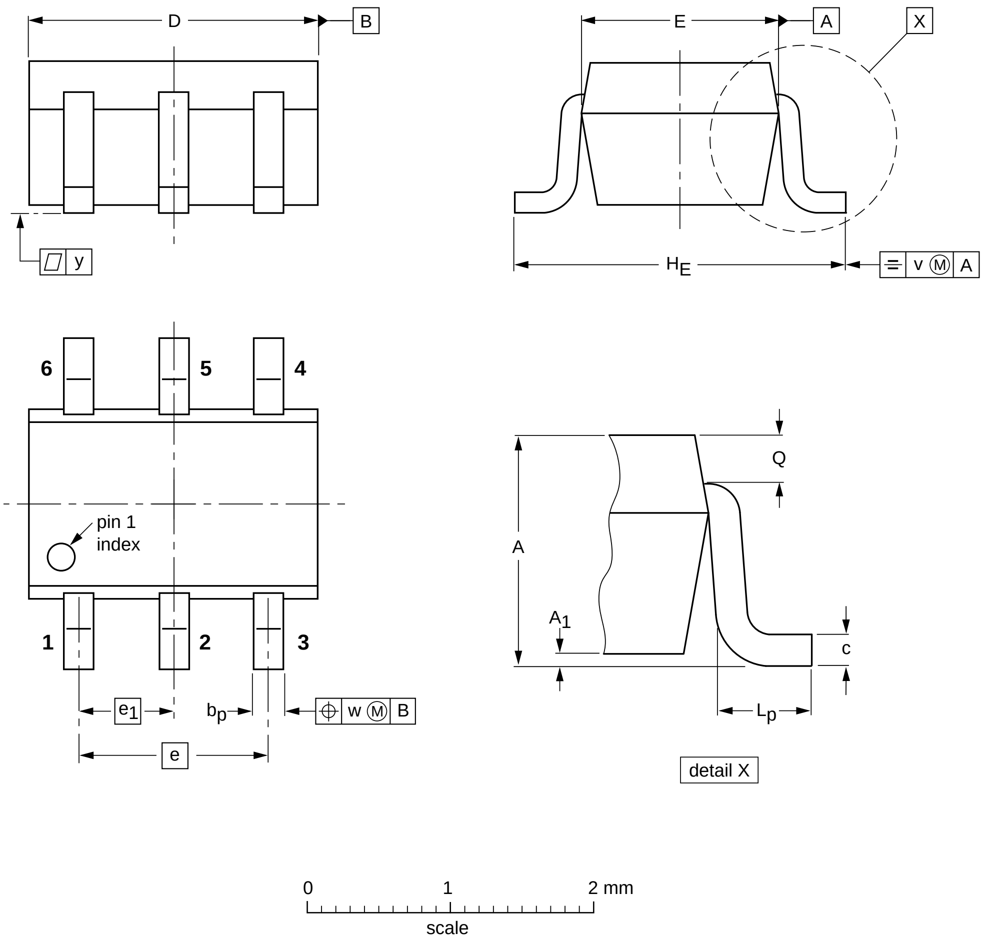


I_D = 1 A; V_{DD} = 30 V

Fig 13. Gate-source voltage as a function of gate charge; typical values

7. Package outline

Plastic surface-mounted package; 6 leads **SOT363**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

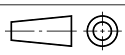
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT363			SC-88			~~04-11-08~~ 06-03-16

Fig 14. Package outline SOT363 (SC-88)

8. Soldering

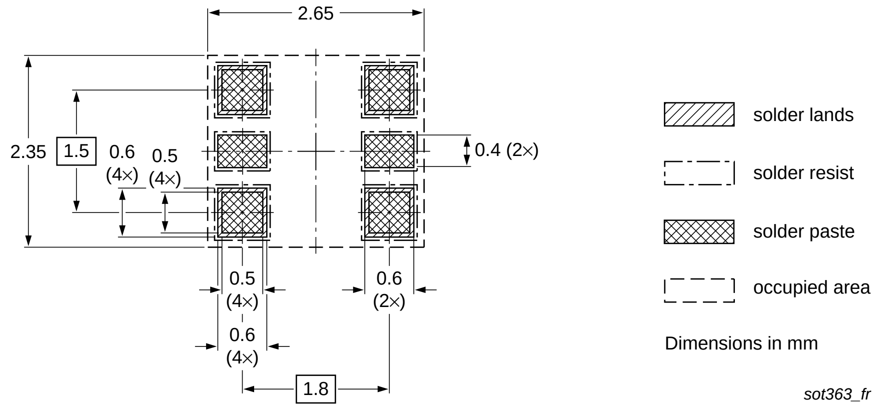


Fig 15. Reflow soldering footprint SOT363 (SC-88)

9. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMGD780SN_2	20100419	Product data sheet	-	PMGD780SN_1
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Table 5 "Characteristics": added $V_{GS(th)}$ maximum value at condition T_j = 25 °C • Section 10 "Legal information": updated			
PMGD780SN_1	20040211	Product data	-	-

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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12. Contents

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